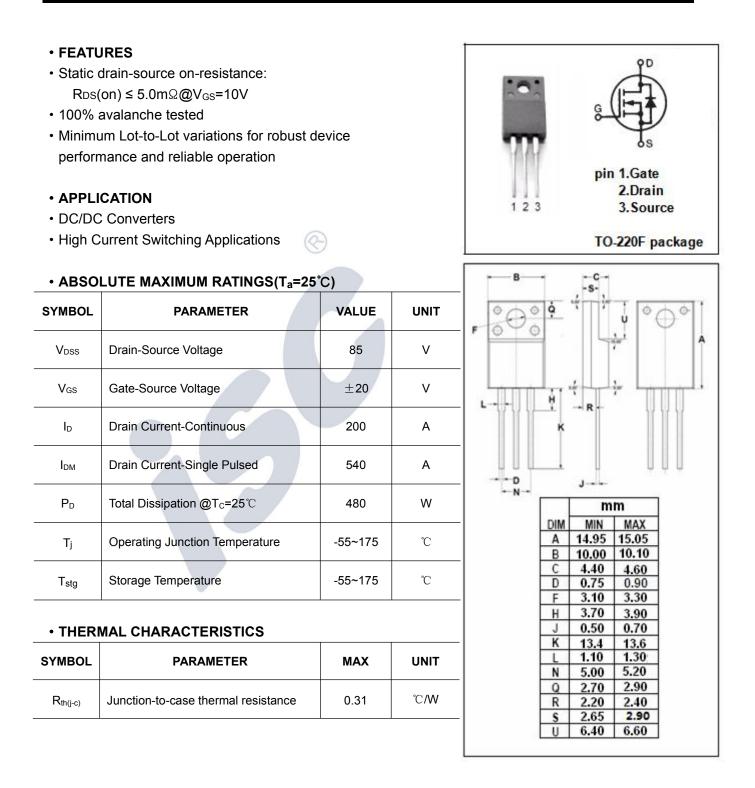


### INCHANGE SEMICONDUCTOR

# isc N-Channel MOSFET Transistor

### IXTC200N085T



1



## isc N-Channel MOSFET Transistor

# IXTC200N085T

#### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0V; ID = 250 μ A	85		V
$V_{GS(th)}$	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; ID = 250 μ A	2.0	4.0	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> = 25A		5.0	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> =0V		±200	nA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V		5	- μΑ
		V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V;T <sub>J</sub> = 150°C		250	
Vsd	Diode forward voltage	I <sub>F</sub> = 25A; V <sub>GS</sub> = 0V		1.0	V

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